

# Frederic Wrobel

## List of Publications by Year in descending order

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35  
papers

640  
citations

623734

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h-index

580821

25  
g-index

35  
all docs

35  
docs citations

35  
times ranked

491  
citing authors

| #  | ARTICLE  | IF  | CITATIONS |
|----|--|-----|-----------|
| 1  | Impact of Atmospheric and Space Radiation on Sensitive Electronic Devices. , 2022, , .   |     | 4         |
| 2  | 0.1â€“10 MeV Neutron Soft Error Rate in Accelerator and Atmospheric Environments. IEEE Transactions on Nuclear Science, 2021, 68, 873-883.   | 2.0 | 18        |
| 3  | Neutron-Induced Failure Dependence on Reverse Gate Voltage for SiC Power MOSFETs in Atmospheric Environment. IEEE Transactions on Nuclear Science, 2021, 68, 1623-1632.                  | 2.0 | 11        |
| 4  | Reliability-driven pin assignment optimization to improve in-orbit soft-error rate. Microelectronics Reliability, 2020, 114, 113885.   | 1.7 | 0         |
| 5  | Design exploration of majority voter architectures based on the signal probability for TMR strategy optimization in space applications. Microelectronics Reliability, 2020, 114, 113877. | 1.7 | 5         |
| 6  | Thermal Neutron-Induced SEUs in the LHC Accelerator Environment. IEEE Transactions on Nuclear Science, 2020, 67, 1412-1420.  | 2.0 | 14        |
| 7  | Analysis of SET Propagation in a System in Package Point of Load Converter. IEEE Transactions on Nuclear Science, 2020, 67, 1494-1502.   | 2.0 | 7         |
| 8  | Exploiting Transistor Folding Layout as RHBD Technique Against Single-Event Transients. IEEE Transactions on Nuclear Science, 2020, 67, 1581-1589.                                       | 2.0 | 4         |
| 9  | Direct Ionization Impact on Accelerator Mixed-Field Soft-Error Rate. IEEE Transactions on Nuclear Science, 2020, 67, 345-352.  | 2.0 | 12        |
| 10 | Mitigation and Predictive Assessment of SET Immunity of Digital Logic Circuits for Space Missions. Aerospace, 2020, 7, 12.   | 2.2 | 5         |
| 11 | Impact of Electrical Stress and Neutron Irradiation on Reliability of Silicon Carbide Power MOSFET. IEEE Transactions on Nuclear Science, 2020, 67, 1365-1373.                           | 2.0 | 16        |
| 12 | Impact of Complex Logic Cell Layout on the Single-Event Transient Sensitivity. IEEE Transactions on Nuclear Science, 2019, 66, 1465-1472.  | 2.0 | 7         |
| 13 | Radiation hardening efficiency of gate sizing and transistor stacking based on standard cells. Microelectronics Reliability, 2019, 100-101, 113457.                                      | 1.7 | 8         |
| 14 | Investigation on Passive and Autonomous Mode Operation of Floating Gate Dosimeters. IEEE Transactions on Nuclear Science, 2019, 66, 1620-1627.   | 2.0 | 10        |
| 15 | SEE Flux and Spectral Hardness Calibration of Neutron Spallation and Mixed-Field Facilities. IEEE Transactions on Nuclear Science, 2019, 66, 1532-1540.                                  | 2.0 | 12        |
| 16 | Impact of Energy Dependence on Ground Level and Avionic SEE Rate Prediction When Applying Standard Test Procedures. Aerospace, 2019, 6, 119.   | 2.2 | 4         |
| 17 | Analysis of Single-Event Effects in DDR3 and DDR3L SDRAMs Using Laser Testing and Monte-Carlo Simulations. IEEE Transactions on Nuclear Science, 2018, 65, 262-268.                      | 2.0 | 4         |
| 18 | Single-Event Effects in the Peripheral Circuitry of a Commercial Ferroelectric Random Access Memory. IEEE Transactions on Nuclear Science, 2018, 65, 1708-1714.                          | 2.0 | 12        |

| #  | ARTICLE   | IF  | CITATIONS |
|----|---|-----|-----------|
| 19 | Analysis of the charge sharing effect in the SET sensitivity of bulk 45nm standard cell layouts under heavy ions. Microelectronics Reliability, 2018, 88-90, 920-924.       | 1.7 | 12        |
| 20 | Floating Gate Dosimeter Suitability for Accelerator-like Environments. IEEE Transactions on Nuclear Science, 2017, , 1-1.   | 2.0 | 21        |
| 21 | The Power Law Shape of Heavy Ions Experimental Cross Section. IEEE Transactions on Nuclear Science, 2017, 64, 427-433.  | 2.0 | 3         |
| 22 | Investigation on the Sensitivity Degradation of Dosimeters based on Floating Gate Structure. , 2017, , .  |     | 1         |
| 23 | SEL Hardness Assurance in a Mixed Radiation Field. IEEE Transactions on Nuclear Science, 2015, 62, 2555-2562.   | 2.0 | 30        |
| 24 | SEL Cross Section Energy Dependence Impact on the High Energy Accelerator Failure Rate. IEEE Transactions on Nuclear Science, 2014, 61, 2936-2944.                          | 2.0 | 22        |
| 25 | Energy Dependence of Tungsten-Dominated SEL Cross Sections. IEEE Transactions on Nuclear Science, 2014, 61, 2718-2726.  | 2.0 | 25        |
| 26 | Dynamic Test Methods for COTS SRAMs. IEEE Transactions on Nuclear Science, 2014, 61, 3095-3102.   | 2.0 | 26        |
| 27 | Multiple Cell Upset Classification & in Commercial SRAMs. IEEE Transactions on Nuclear Science, 2014, 61, 1747-1754.  | 2.0 | 46        |
| 28 | Determining Realistic Parameters for the & Double Exponential Law that Models & Transient Current Pulses. IEEE Transactions on Nuclear Science, 2014, 61, 1813-1818.        | 2.0 | 36        |
| 29 | Gate Voltage Contribution to Neutron-Induced SEB of Trench Gate Fieldstop IGBT. IEEE Transactions on Nuclear Science, 2014, 61, 1739-1746.                                  | 2.0 | 6         |
| 30 | Anthology of the Development of Radiation Transport Tools as Applied to Single Event Effects. IEEE Transactions on Nuclear Science, 2013, 60, 1876-1911.                    | 2.0 | 119       |
| 31 | A Simple Method for Assessing Power Devices Sensitivity to SEEs in Atmospheric Environment. IEEE Transactions on Nuclear Science, 2013, 60, 2559-2566.                      | 2.0 | 7         |
| 32 | Post-Irradiation-Gate-Stress on Power MOSFETs: Quantification of Latent Defects-Induced Reliability Degradation. IEEE Transactions on Nuclear Science, 2013, 60, 4166-4174. | 2.0 | 6         |
| 33 | MC-ORACLE: A tool for predicting Soft Error Rate. Computer Physics Communications, 2011, 182, 317-321.  | 7.5 | 45        |
| 34 | Detailed history of recoiling ions induced by nucleons. Computer Physics Communications, 2008, 178, 88-104.   | 7.5 | 19        |
| 35 | Criterion for SEU occurrence in SRAM deduced from circuit and device Simulations in case of neutron-induced SER. IEEE Transactions on Nuclear Science, 2005, 52, 1148-1155. | 2.0 | 63        |